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(54) Title: SILICON CARBIDE (SiC) WAFER POLISHING WITH SLURRY FORMULATION AND PROCESS

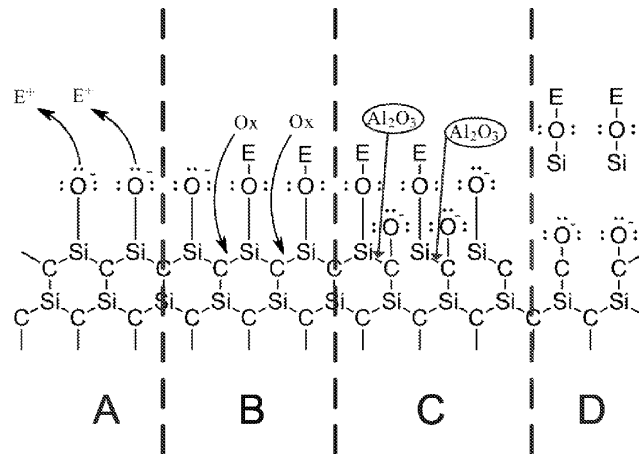


FIG. 1

(57) Abstract: A method for polishing a silicon carbide surface. The silicon carbide surface is polished with a particulate abrasive while exposed to a composition of water, an oxidizing agent and an electrophile. The method provides material removal rates (MRR) that are competitive with, or superior to, conventional methods without utilizing harsh chemicals.

[Continued on next page]

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